UNIVERSITI PUTRA MALAYSIA

EFFECT OF ALKALINE EARTH METAL (M= Sr, Ca and Mg) SUBSTITUTION ON DIELECTRIC PROPERTIES OF Ba_{1-x}M_xPbO_3 CERAMICS

ARI SULISTYO RINI

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By

ARI SULISTYO RINI

Thesis Submitted to the School of Graduate Studies, Universiti Putra Malaysia, in Fulfilment of Requirement for the Degree of Master of Science

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Chairman: Associate Professor Wan Mohd. Daud Wan Yusoff, Ph.D.

Faculty: Science and Environmental Studies

BaPbO$_3$-based ceramic have been the subject of numerous laboratory investigations, structurally and electrically. BaPbO$_3$ is a polycrystalline that possesses perovskite crystal structure, which is similar to the prototype dielectric ceramic i.e. BaTiO$_3$ structure. It is obviously noticed that suitable substitution on a system, enables us to change electrical properties of material to obtain specific requirement.

In this work, alkaline earth metals (i.e. Sr, Ca and Mg) were used as substitution elements. The substitution, which are based on ionic radii consideration ($r_{Mg} < r_{Ca} < r_{Sr}$), are attempted to drive the metallic properties of BaPbO$_3$ towards a semiconductor by creating either oxygen vacancies and/or allowing partial reduction of Pb$^{4+}$ to Pb$^{2+}$ thereby stabilizing the unusual 3+ intermediate valency for Pb in the lattice. Dielectric studies of Ba$_{1-x}$M$_x$PbO$_3$ system (M = Mg, Sr and Ca) have not been reported so far.
The experimental investigation is divided into two categories. Firstly, x-ray diffraction methods and microstructural investigation, which is considered important in order to provide supportive evidence to any proposed model of dielectric behaviour. Secondly, the main experiment consists of alternating current conductivity measurement. Electrical tests on materials investigate their ability to store charge (capacitance) and transfer charge (conductance). Analyzing these parameters can provide valuable information in terms of a material's physical and chemical properties.

The results of XRD reveals lattice parameter changes of $\text{BaPbO}_3$ after substitution of $\text{Sr}^{2+}, \text{Ca}^{2+}$ and $\text{Mg}^{2+}$. Structural transitions were only detected from orthorhombic perovskite to pseudo-cubic perovskite after substituted by 70 mol% of Mg at Ba-site. It is obviously noticed that to maintain molecule constancy of the chemical reaction of $\text{Ba}_{1-x}\text{Mg}_{x}\text{PbO}_{3-x}$ indicate oxygen deficiency on the product. From SEM Micrograph, it is clearly seen that, the samples prepared after calcined and sintered at 800 °C for 6 hours and 850 °C for 24 hours respectively, still contain high porosity.

The experimental results of deduced dielectric response from ac conductivity measurement were then separated into two regions, i.e. bulk response and grain boundary response, using equivalent electrical circuit model. Effect of porosity was detected from the grain boundary response at low frequency region that dominated by dc conduction or hopping charge carrier at all range of sample. The bulk response that represented by high frequency region indicated the less dispersion behaviour.
Substitution of Sr$^{2+}$, Ca$^{2+}$ and Mg$^{2+}$ into Ba-site of BaPbO$_3$ has increased the resistivity and the dielectric constant of pure BaPbO$_3$. Substitution of Ca$^{2+}$ has apparently give major contribution to increase the dielectric constant of BaPbO$_3$ as high as $7\times10^4$ when substituted by 60 mol% of Ca$^{2+}$ at Ba-site of BaPbO$_3$. 
Abstrak tesis yang dikemukakan kepada Senat Universiti Putra Malaysia sebagai memenuhi keperluan untuk ijazah Master Sains

KESAN PENDOPAN METAL ALKALI TANAH (M= Sr, Ca, dan Mg) TERHADAP CIRI-CIRI DIELEKTRIK SERAMIK Ba$_{1-x}$M$_x$PbO$_3$

Oleh

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Ogos 2002
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Seramik berasaskan BaPbO$_3$ telah banyak dilakukan penyelidikan keatasnya secara struktur dan kemampuannya untuk menghantarkan arus elektrik. BaPbO$_3$ adalah sejenis poli-hablur yang mempunyai struktur hablur perovskite, dimana ia mempunyai persamaan dalam seramik dielektrik prototype, sebagai contohnya struktur BaTiO$_3$. Dapat dipahami bahawa pengganti yang sesuai dalam sistem memungkinkan kita untuk mengubah benda yang bermuatan elektrik; yang pada akhirnya mendapatkan sesuai dengan yang diharapkan.

Dalam kajian ini, unsur alkali tanah (seperti Sr, Ca, dan Mg) telah digunakan sebagai elemen gantian. Bahan penggantian berasaskan jejari ion (r$_{Mg}<r_{Ca}<r_{Sr}$) adalah untuk mengubah bahan pengalir kepada bahan semikonduktor. Setakat ini, kajian mengenai dielektrik pada sistem Ba$_{1-x}$M$_x$PbO$_3$ (M=Sr, Ca, dan Mg) masih belum dilaporkan.

Keputusan XRD menunjukkan bahawa parameter kekisi BaPbO₃ berubah selepas digantikan oleh Sr²⁺, Ca²⁺, dan Mg²⁺. Struktur transisi hanya dapat dikesan dari orthorhombik perovskite kepada pseudo-kubus perovskite selepas digantikan dengan 70 mol% Mg pada tapak Ba. Adalah jelas bahawa untuk mengekalkan konsistensi molekul pada tindakbalas kimia BaPbO₃ dicirikan dengan kekurangan oksigen pada produk. Daripada mikrograf SEM, dapat dilihat sampel yang disediakan selepas pengkalsinan pada 800°C selama 6 jam dan persinteran 850°C selama 24 jam, masih mempunyai keadaan berongga yang tinggi.

Dari keputusan eksperimen, sambutan dielektrik yang dideduksikan daripada pengukuran pengaliran arus ulang-alik, kemudian dibahagikan kepada dua bahagian, iaitu sambutan pukal dan sambutan sempadan butiran menggunakan model litar elektrik yang sepadan. Kesan keronggaan telah dikesan dari sambutan sepadan butiran bahagian frekuensi rendah yang didominasi oleh pengaliran arus terus atau pembawa cas loncatan pada pelbagai jenis sampel. Sambutan pukal yang diwakili oleh bahagian frekuensi tinggi dicirikan dengan sifat pengukuran penyebaran.

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Penggantian Sr, Ca, Mg ke dalam tapak Ba pada BaPbO₃ telah meningkatkan ketahanan dan pemalar dielektrik BaPbO₃ sehingga $7 \times 10^4$ apabila digantikan dengan 60 mol% Ca²⁺ pada tapak Ba.
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I certify that an Examination Committee met on 29th August 2002 to conduct the final examination of Ari Sulisty Rini on her Master of Science thesis entitled “Effect of Alkaline Earth Metal Substitution (M= Sr, Ca and Mg) on Dielectric Properties of Ba$_{1-x}$M$_x$PbO$_3$ Ceramics” in accordance with Universiti Pertanian Malaysia (Higher Degree) Act 1980 and Universiti Pertanian Malaysia (Higher Degree) Regulation 1981. The Committee recommends that the candidate be awarded the relevant degree. Members of the Examination Committee are as follows:

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Date:
DECLARATION

I hereby declare that the thesis is based on my original work except for quotations and citations which have been duly acknowledged. I also declare that it has not been previously or concurrently submitted for any other degree at UPM or other institutions.

ARI SULISTYO RINI

Date: 14 Sept 2002
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\( \alpha \)  
spectral parameter

\( \varepsilon \)  
dielectric permittivity (F/m)

\( \varepsilon_{inf} \)  
dielectric permittivity at very high frequency

\( \varepsilon_r \)  
relative dielectric permittivity

\( \varepsilon^* (\omega) \)  
complex permittivity as a function of angular frequency

\( \varepsilon' (\omega) \)  
the real part of complex permittivity as a function of angular frequency

\( \varepsilon'' (\omega) \)  
the imaginary part of complex permittivity as a function of angular frequency

\( \chi^* (\omega) \)  
complex dielectric susceptibility

\( \chi' \)  
real part of dielectric susceptibility

\( \chi'' \)  
imaginary part of dielectric susceptibility

\( \lambda \)  
wave length

\( \mu \)  
micron

\( \rho \)  
resistivity (ohm/cm)

\( \sigma \)  
conductivity (mho/cm)

\( \sigma (\omega) \)  
conductivity as a function of angular frequency

\( \tau \)  
relaxation time (sec)

\( \omega \)  
angular frequency

\( \omega_p \)  
peak angular frequency

\( \omega_c \)  
critical angular frequency

\( \propto \)  
proportional to
Å  Angstrom unit
a, b, c  lattice parameters
eV  electron volt
exp  exponential
f  frequency
h, k, l  Miller indices
j  = √-1
k  Boltzmann constant
kHz  kilohertz
ln  natural logarithm
log  logarithm
mHz  millihertz
Ac  alternating current
B  susceptance (mho)
C  capacitance
C'  real part of capacitance
C''  imaginary part of capacitance
DC  direct current
E  activation energy
FRA  Frequency Response Analyzer
G  Conductance
HP  Hewlett Packard
Hz  Hertz
I  current
Im  imaginary part
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<td>XRD</td>
<td>x-ray diffraction</td>
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<tr>
<td>Y</td>
<td>admittance</td>
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<td>Y'</td>
<td>real part of admittance</td>
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<td>Y&quot;</td>
<td>imaginary part of admittance</td>
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<td>Y*</td>
<td>complex admittance</td>
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<td>Z</td>
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<td>Z'</td>
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<td>Z*</td>
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INTRODUCTION

Evolution of electronic component and demands for advanced materials yield intensive investigations on electrical and structural properties of materials. Characterization and identification of physical phenomena of materials become more interesting as new theories emerge to explain the observed experimental phenomena.

Among the phenomena that are, being intensely characterized is the electrical behaviour. The electrical tests on materials reveal their ability to store (capacitance) and transfer charge (conductance). Analyzing these phenomena can provide valuable information in terms of a material's physical and chemical properties including: impedance, porosity, tan delta, molecular relaxation, grain boundaries, phase changes, permittivity and modulus, along with many other parameters.

BaPbO₃-based ceramic have been the subject of numerous structural and electrical investigations. BaPbO₃ is a polycrystalline that possesses perovskite crystal structure, which is similar to the prototype dielectric ceramic i.e. BaTiO₃ structure. The discovery of superconductivity of Ba-Pb-Bi-O system has led to wide range of research on BaPbO₃-based system, included BaPbO₃ itself, though report of superconductivity below ~0.4 K in BaPbO₃ has not been confirmed by more recent studies (Mattheis 1990).

BaPbO₃ shows a metallic behaviour although there is no transition-metal ion present, and its resistivity has a small temperature dependent part. It is obviously
noticed that suitable substitution on a system, enables us to change electrical properties of material to obtain specific requirement. For example, after Bi was doped into the Pb sites, superconductivity occurred at about 13 K along with a metal-insulator transition, which coincided with structural changes, whereas when Sb was introduced into Pb sites, no MI transition was found (Zhao 2000).

Alkaline earth metals (i.e. Ba, Mg, Sr, and Ca) were widely used as substitution elements. In some cases, they have been found to improve the electrical properties of Ba-based and Pb-based system to a specific requirement. Literature review on Mg, Sr, and Ca doped on Ba-site of BaPbO$_3$ were still sparse. What available is only limited to high-temperature thermoelectric properties of Ba-Sr-Pb-O and Positive Temperature Coefficient of Resistivity of Ba-Sr-Pb-O. Dielectric studies of Ba$_{1-x}$M$_x$PbO$_3$ system (M = Mg, Sr and Ca) have not been reported so far.

The substitution, which are based on ionic radii consideration ($r_{Mg} < r_{Ca} < r_{Sr}$), is an attempt to drive the metallic properties of BaPbO$_3$ towards a semiconductor by creating either oxygen vacancies and/or allowing partial reduction of Pb$^{4+}$ to Pb$^{2+}$ there by stabilizing the unusual 3+ intermediate valency for Pb in the lattice (Kodenkandath 2000).

**Dielectric Analysis**

Impedance Analysis is a powerful non-destructive tool for analyzing a range of electroceramic materials. The advantage of this technique is that it yields accurate and repeatable results, which are unobtainable by other electrical means. The properties of ceramic materials depend on close control of their structure in terms of